

AMENDMENTS TO THE SPECIFICATION:

Please amend ¶ [0082] on page 41 of the Specification as follows:

In the ion implantation apparatus of the present invention, it is also possible to provide means for measuring physical quantities such as densities, energies, and the like of ions and electrons in plasma, so as to control a process condition based on the measured physical quantities. For example, it is possible to arrange, at a front face of a deposition-assistance substrate, a Langmuir ~~prove~~probe as means for measuring an electron density in plasma, in a manner to measure an electric current based on electrons flowing through the ~~prove~~probe by a ~~prove~~probe electric current measurement device, thereby measuring the electron density in the plasma. Depending on the measured values, it is possible to control a bias voltage to be applied to the deposition-assistance substrate, thereby further optimizing a yield of containing-fullerene. As a control method of a bias voltage, it is possible to manually control a bias voltage by an operator after viewing the measured values, or to conduct automatic control by a computer.